

**isc Silicon NPN Power Transistors**

**BUX67/A/B/C**

**DESCRIPTION**

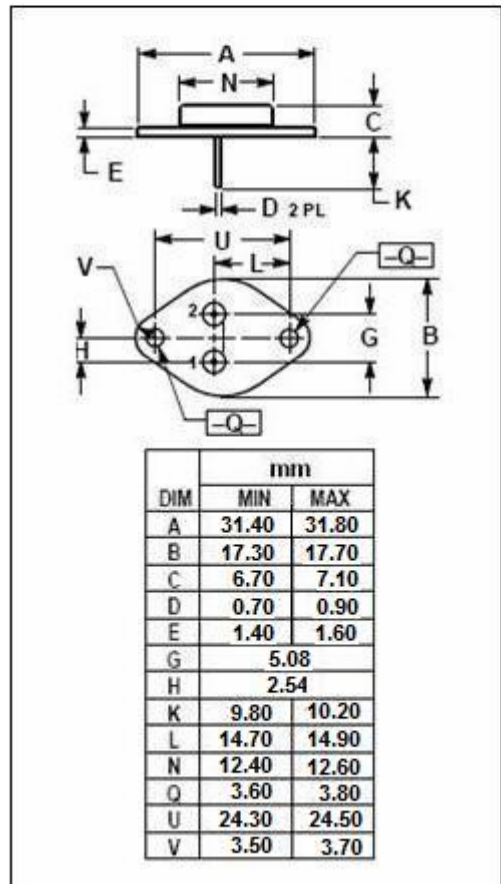
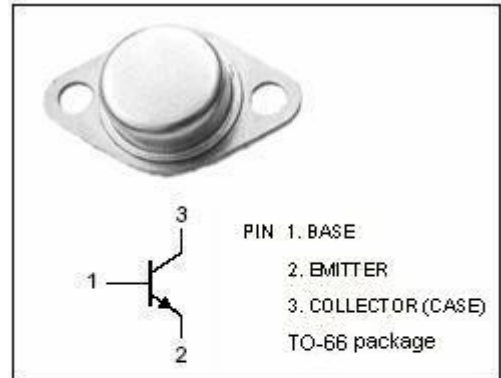
- Continuous Collector Current- $I_C= 2A$
- Power Dissipation- $P_D=35W @T_C= 25^\circ C$
- Collector-Emitter Saturation Voltage-  
:  $V_{CE(sat)}= 2.5V(Max) @ I_C = 1A$

**APPLICATIONS**

- Designed for high-speed switching and linear amplifier application for high-voltage operational amplifiers, switching regulators, converters, deflection stages and high fidelity amplifiers.

**ABSOLUTE MAXIMUM RATINGS( $T_a=25^\circ C$ )**

SYMBOL	PARAMETER		VALUE	UNIT
$V_{CBO}$	Collector-Base Voltage	BUX67	200	V
		BUX67A	300	
		BUX67B	350	
		BUX67C	400	
$V_{CEO}$	Collector-Emitter Voltage	BUX67	150	V
		BUX67A	250	
		BUX67B	300	
		BUX67C	350	
$V_{EBO}$	Emitter-Base Voltage		6	V
$I_C$	Collector Current-Continuous		2.0	A
$I_{CP}$	Collector Current-Peak		5.0	A
$I_B$	Base Current		1.0	A
$P_C$	Collector Power Dissipation@ $T_C=25^\circ C$		35	W
$T_J$	Junction Temperature		200	$^\circ C$
$T_{stg}$	Storage Temperature		-65~200	$^\circ C$



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## ELECTRICAL CHARACTERISTICS

 $T_C=25^\circ\text{C}$  unless otherwise specified

SYMBOL	PARAMETER		CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	BUX67	$I_C=200\text{mA}; I_B=0$	150			V
		BUX67A		250			
		BUX67B		300			
		BUX67C		350			
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage		$I_C=1\text{A}; I_B=0.15\text{A}$			2.5	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage		$I_C=1\text{A}; I_B=0.15\text{A}$			1.4	V
$I_{CBO}$	Collector Cutoff Current	BUX67	$V_{CB}=150\text{V}; I_E=0$			1.0	mA
		BUX67A	$V_{CB}=250\text{V}; I_E=0$			1.0	
		BUX67B	$V_{CB}=300\text{V}; I_E=0$			1.0	
		BUX67C	$V_{CB}=350\text{V}; I_E=0$			1.0	
$I_{EBO}$	Emitter Cutoff Current		$V_{EB}=6\text{V}; I_C=0$			0.5	mA
$h_{FE}$	DC Current Gain		$I_C=1\text{A}; V_{CE}=5\text{V}$	10		150	
$f_T$	Current Gain-Bandwidth Product		$I_C=0.5\text{A}; V_{CE}=10\text{V}$		25		MHz